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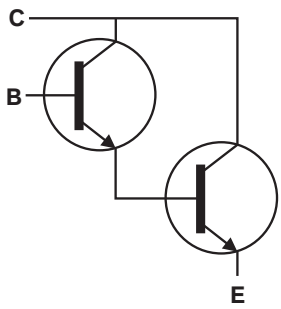
FMMT634 100V NPN DARLINGTON TRANSISTOR IN SOT23

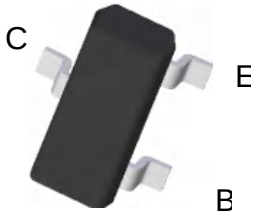


Features

- BV_{CEO} > 100V
- I_C = 900mA high Continuous Collector Current
- I_{CM} = 5A Peak Pulse Current
- 625mW Power dissipation
- h_{FE} > 5k up to 2A for high current gain hold up
- Complementary PNP Type: FMMT734
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Applications

- Lamp
- Relay
- Solenoid Driving



SOT23

Marking 634

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See ty/lead_free.html for more information about Diodes Incorporated’s definitions of Halogen an d Antimony free, "Green" and Lead-Free.
3. Halogen and Antimony free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details,

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	12	V
Continuous Collector Current	I_C	900	mA
Peak Pulse Current	I_{CM}	5	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	625	mW
Power Dissipation (Note 6)	P_D	806	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	155	°C/W
Thermal Resistance, Junction to Leads (Note 7)	$R_{\theta JL}$	194	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	2,000	V	2
Electrostatic Discharge - Machine Model	ESD MM	200	V	B

Notes:
5. For a device mounted with the exposed collector pad on 25mm x 25mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Same as note (5), except the device is measured at t ≤ 5 sec.
7. Thermal resistance from junction to solder-point (at the end of the collector lead).
8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

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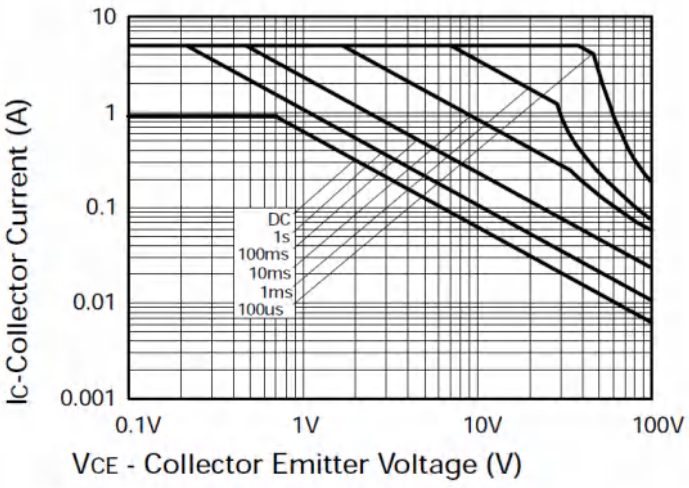
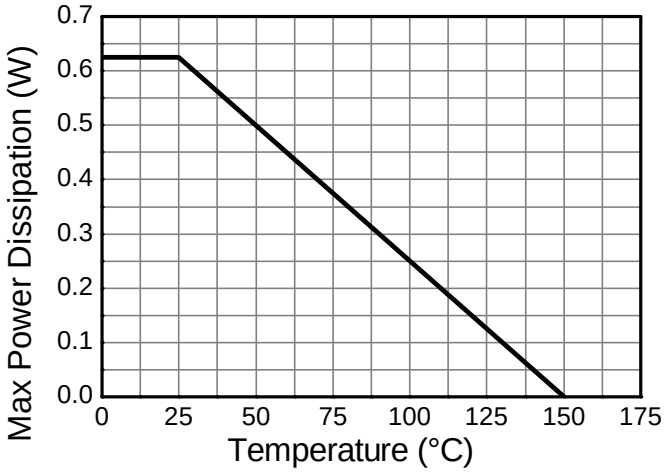
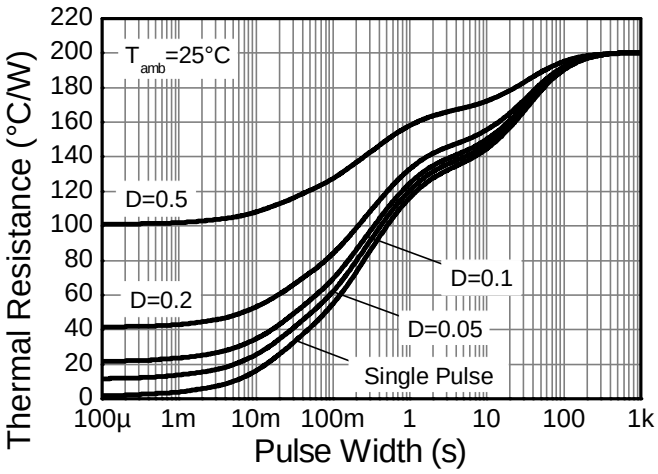
Thermal Characteristics and Derating information



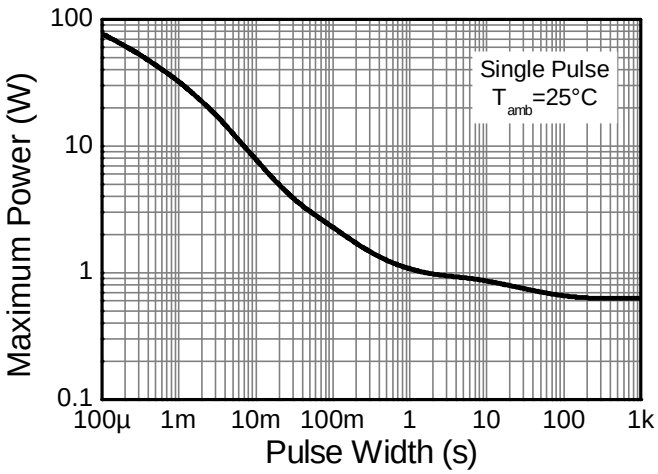
Safe Operating Area



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

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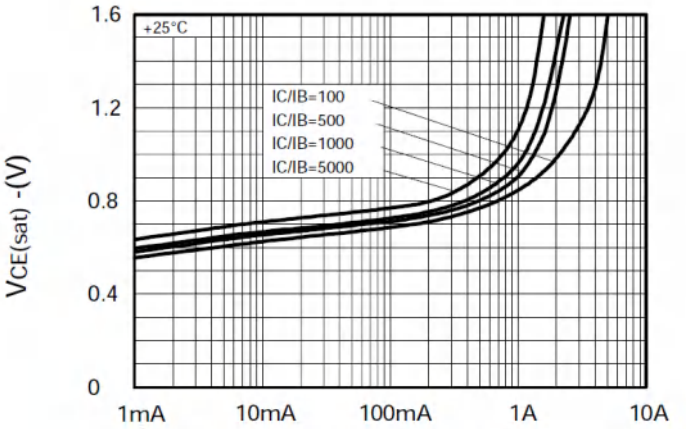
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

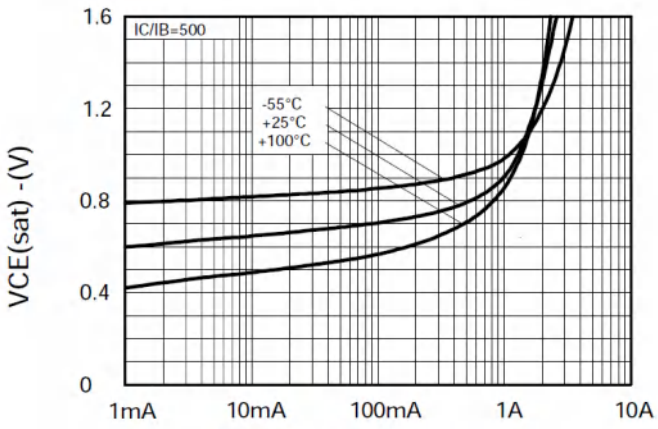
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	120	170	-	V	I_C = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	100	115	-	V	I_C = 10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	12	16	-	V	I_E = 100μA
Collector Cut-off Current	I_{CBO}	-	<1	10	nA	V_{CB} = 80V
Emitter Cut-off Current	I_{EBO}	-	<1	10	nA	V_{EB} = 7V
Collector Emitter Cut-off Current	I_{CES}	-	<1	100	nA	V_{CES} = 80V
Static Forward Current Transfer Ratio (Note 9)	h_{FE}	- 20k 15k 5k - -	50k 60k 40k 14k 24k 600	- - - - - -	-	I_C = 10mA, V_{CE} = 5V I_C = 100mA, V_{CE} = 5V I_C = 1A, V_{CE} = 5V I_C = 2A, V_{CE} = 5V I_C = 1A, V_{CE} = 2V I_C = 5A, V_{CE} = 5V
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	- - - - - -	0.67 0.72 0.75 0.82 0.68 0.85	0.75 0.80 0.85 0.93 - 0.96	V	I_C = 100mA, I_B = 1mA I_C = 250mA, I_B = 1mA I_C = 500mA, I_B = 5mA I_C = 900mA, I_B = 5mA I_C = 900mA, I_B = 5mA, T_J=+150°C I_C = 1A, I_B = 5mA
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	-	1.5	1.65	V	I_C = 1A, I_B = 5mA
Base-Emitter Turn-On Voltage (Note 9)	$V_{BE(on)}$	-	1.33	1.50	V	I_C = 1A, V_{CE} = 5V
Transition Frequency	f_T	-	140	-	MHz	I_C = 50mA, V_{CE} = 10V, f = 100MHz
Output Capacitance	C_{obo}	-	9	20	pF	V_{CB} = 10V, f = 1MHz
Turn-On Time	$t_{(on)}$	-	290	-	ns	V_{CC} = 20V, I_C = 500mA, I_{B1} = -I_{B2} = 1mA
Turn-Off Time	$t_{(off)}$	-	2,400	-	ns	

Notes: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%

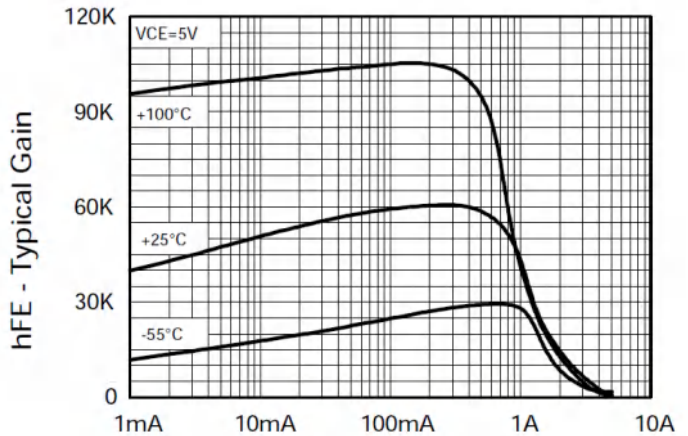
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



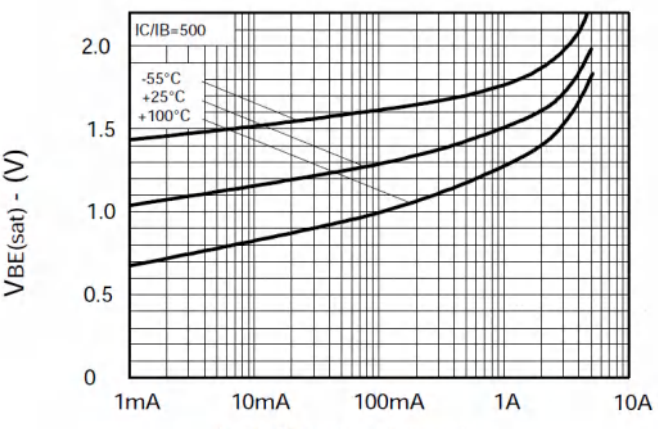
VCE(sat) v IC



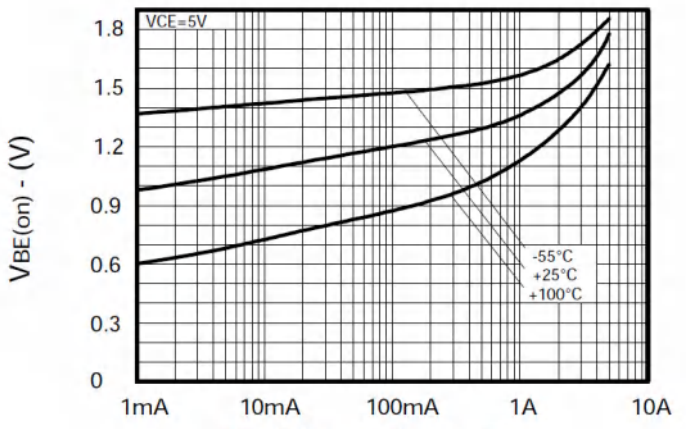
VCE(sat) v IC



hFE V IC



VBE(sat) v IC



VBE(on) v IC

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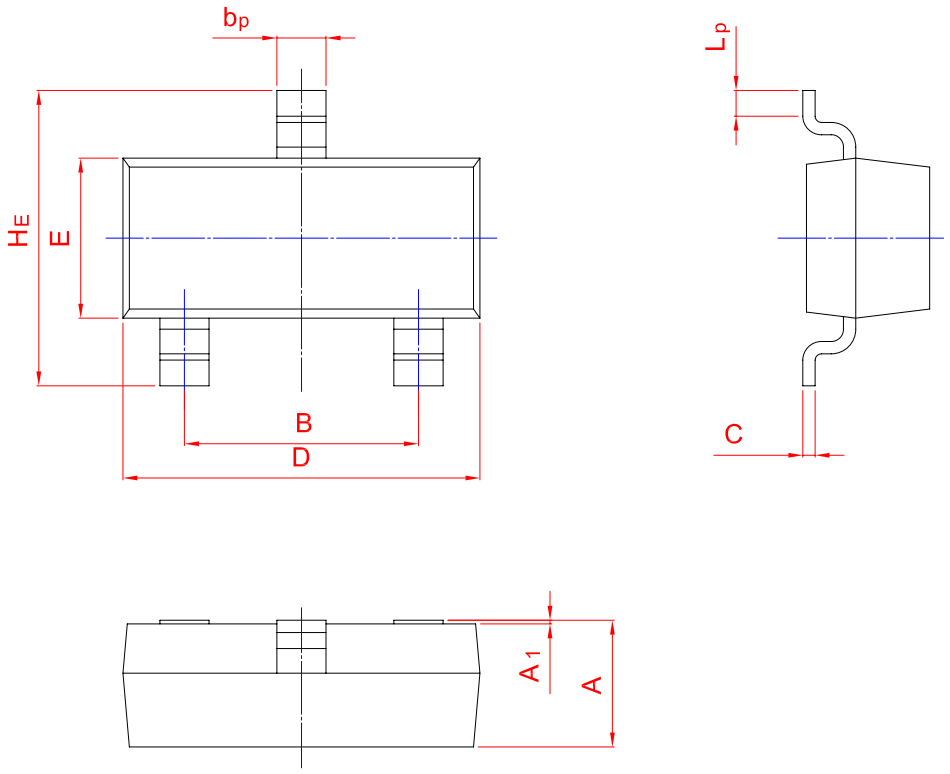
PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT-23**



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20